

	L #	Hits	Search Text	DBs
1	L1	143555	"438"/\$.cccls.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	192	1 and (plasma near etch\$3) near polysilicon	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	51	2 and HBr	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	3	3 and Cl?	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L5	5	3 and (EEPROM or (flash near memory))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L6	0	5 and (polysilicon near (residue? or spacer))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L7	8	suzuki-tamito.in.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L8	0	7 and etch\$3 near polysilicon	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L9	290	(etch\$3 near polysilicon).ti.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L10	54	9 and (plasma near etch\$3)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
11	L11	22	10 and HBr	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	L12	0	11 and (polysilicon near (residue? or spacer))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	L13	18	11 and (mask or resist)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	L14	7373	(etch\$3 near polysilicon)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
15	L15	3341	14 and plasma	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
16	L16	2812	15 and (mask or resist)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
17	L17	451	16 and (polysilicon near (residue? or spacer or remain\$3))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
18	L19	3	18 and Cl?	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
19	L18	97	17 and HBr	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
20	L20	35	18 and (first and second) near (plasma or etch\$3 or process)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	L #	Hits	Search Text	DBs
21	L22	4	20 and over-etching	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
22	L23	24	18 and third near (plasma or etch\$3 or process)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB